

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-31. (Cancelled)

32. (New). An electronic structure having embedded substantially flush circuit features comprising:

a rigid first dielectric layer of a first polymeric material having a substantially flush first major surface;

a circuitry layer having a substantially flush second major surface formed on said first major surface and a substantially flush third major surface substantially parallel to said second surface; and

a second dielectric layer of a second dielectric polymer having a substantially flush fourth major surface formed on said third surface..

33. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 32, wherein said circuitry layer comprises:

a layer of a third dielectric polymer having circuitry features having sidewalls laser ablated therethrough;

a conductive seed layer formed on said sidewalls;

a film of a conductive material plated on said seed layer, said film having a surface substantially flush with said third major surface.

34. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 32, wherein said first dielectric layer comprises:

a reinforcing material selected from the group consisting of glass fibers and glass fabric.

35. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 32, wherein said dielectric polymers are selected from thermoplastic and thermosetting resins.

36. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 32, wherein said circuitry layer is up to about 20 microns thick.

37. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 33, wherein said conductive material comprises copper.

38. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 32, wherein said circuitry layer is about 5 to about 20 microns thick.

39. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 32, wherein said circuitry layer is about 5 to about 10 microns thick.

40. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 33, wherein said seed layer comprises copper or chromium.

41. (New). The electronic structure having embedded substantially flush circuit features, according to Claim 33, wherein said seed layer is about 100 angstroms to about 5000 angstroms thick.